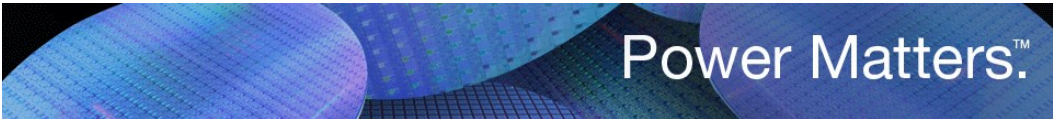


PRODUCTS

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Home / Power Discretes & Modules / BJT(BiPolar Junction Transistor) / PNP Transistor / 2N5092 (#23281)

2N5092 (#23281)

Product Status

In Production

Overview

Diagrams

How to Buy

Related Links

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			0.50	V
DC Current Gain	HFE	50.00		300.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			400.00	V
Collector Current (dc)	I_C			1.00	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			400.00	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			6.00	V
Power Dissipation, Total	P_T			4.00	W

This part can be found in the following product categories:

- Power Discretes & Modules ▶ BJT(BiPolar Junction Transistor) ▶ PNP Transistor